WHAT IS CLAIMED IS:

1. A semiconductor structure, comprising:

   a substrate;

   a metal reflective layer, disposed on a surface of the substrate;

   UV glue, disposed on a surface of the metal reflective layer; and

   an element, adhered to the metal reflective layer through the UV glue with the UV glue between the metal reflective layer and the element, the element being made of light-transparent material for an ultraviolet ray to pass therethrough;

   wherein the UV glue is cured by the ultraviolet ray in a UV-curing process and the metal reflective layer reflects the ultraviolet ray that passes through the element to the metal reflective layer so as to accelerate curing of the UV glue that is between the metal reflective layer and the element.

2. The semiconductor structure according to claim 1, wherein the substrate is a chip.

3. The semiconductor structure according to claim 1, wherein the substrate is a silicon substrate.

4. The semiconductor structure according to claim 1, wherein the element is a fiber array unit.

5. The semiconductor structure according to claim 4, wherein the fiber array unit is a plurality of fibers arranged in a row or a plurality of rows fixed on a carrier.

6. The semiconductor structure according to claim 1, wherein the metal reflective layer has a plurality of holes, the UV glue adhering with the substrate through the holes.

7. The semiconductor structure according to claim 1, wherein the metal reflective layer is a mirror surface.

8. The semiconductor structure according to claim 1, wherein an area between a whole bottom surface of the element and the metal reflective layer is fully filled with the UV glue.